

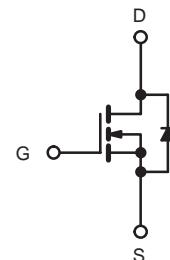
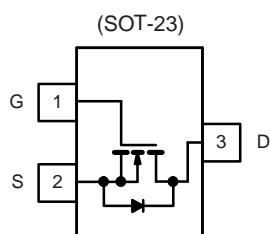
# RU207C-VB Datasheet

## N-Channel 20V (D-S) MOSFET

PRODUCT SUMMARY			
$V_{DS}$ (V)	$R_{DS(on)}$ ( $\Omega$ )	$I_D$ (A) <sup>a, g</sup>	$Q_g$ (Typ.)
20	0.011 at $V_{GS} = 10$ V	9	8nC
	0.012 at $V_{GS} = 4.5$ V	8	

## FEATURES

- Halogen-free According to IEC 61249-2-21 Definition
- Trench Gen III Power MOSFET
- 100 %  $R_g$  Tested
- 100 % UIS Tested
- Compliant to RoHS Directive 2002/95/EC

RoHS  
COMPLIANT

N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS $T_A = 25$ °C, unless otherwise noted				
Parameter	Symbol	Limit	Unit	
Drain-Source Voltage	$V_{DS}$	20	V	
Gate-Source Voltage	$V_{GS}$	$\pm 12$		
Continuous Drain Current ( $T_J = 150$ °C)	$I_D$	$9^a, g$	A	
		6.5 <sup>g</sup>		
		7 <sup>b, c</sup>		
		4.5 <sup>b, c</sup>		
Pulsed Drain Current	$I_{DM}$	32 <sup>g</sup>	A	
Avalanche Current	$I_{AS}$	15		
Avalanche Energy	$E_{AS}$	11.25		mJ
Continuous Source-Drain Diode Current	$I_S$	3 <sup>a, g</sup>		
		1.5 <sup>b, c</sup>		
Maximum Power Dissipation	$P_D$	3.5	W	
		2.0		
		2.3 <sup>b, c</sup>		
		1.0 <sup>b, c</sup>		
Operating Junction and Storage Temperature Range	$T_J, T_{stg}$	- 55 to 150	°C	
Soldering Recommendations (Peak Temperature) <sup>d, e</sup>		260		

THERMAL RESISTANCE RATINGS				
Parameter	Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient <sup>b, f</sup>	$R_{thJA}$	29	36	°C/W
Maximum Junction-to-Case (Drain)	Steady State	$R_{thJC}$	3.6	

Notes:

a. Based on  $T_C = 25$  °C.

b. Surface Mounted on 1" x 1" FR4 board.

c.  $t = 10$  s.

d. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.

e. Rework Conditions: manual soldering with a soldering iron is not recommended for leadless components.

f. Maximum under Steady State conditions is 81 °C/W.

g. Package limited.

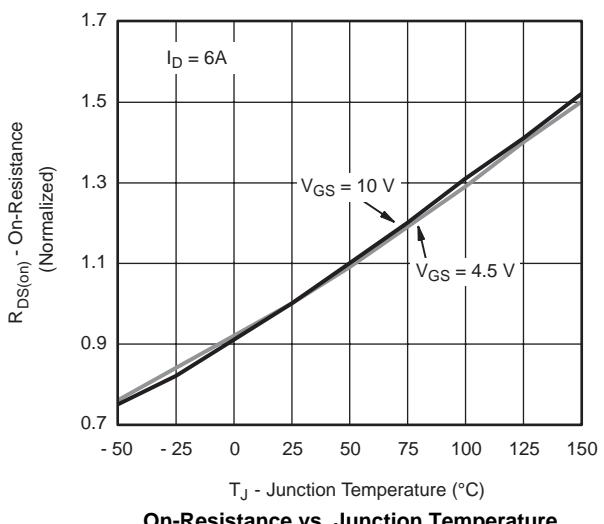
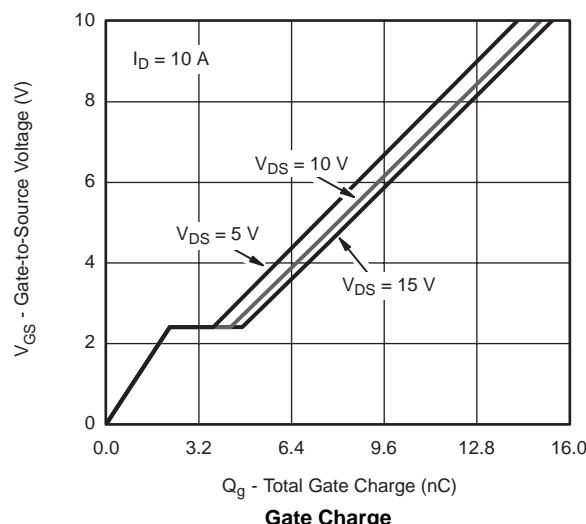
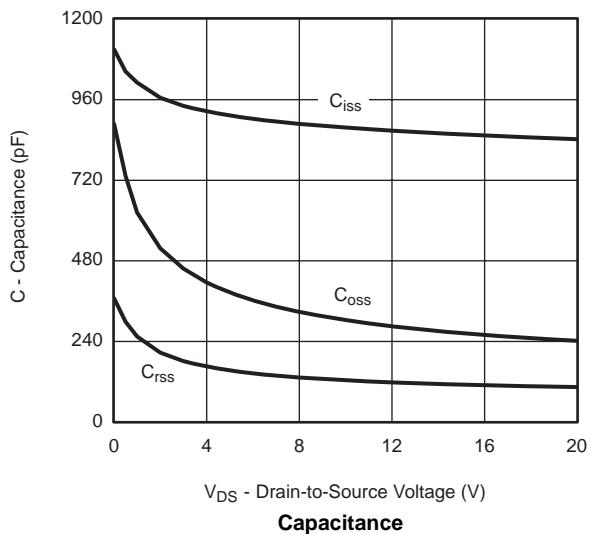
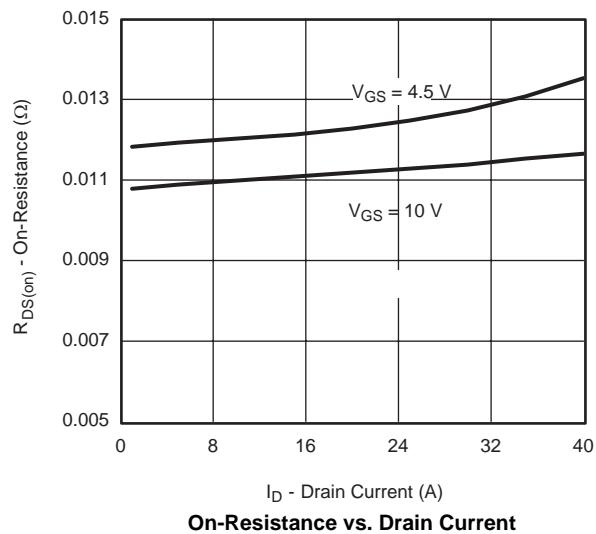
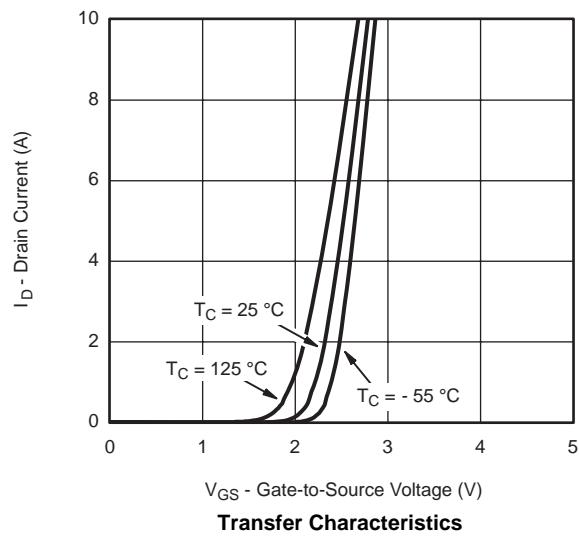
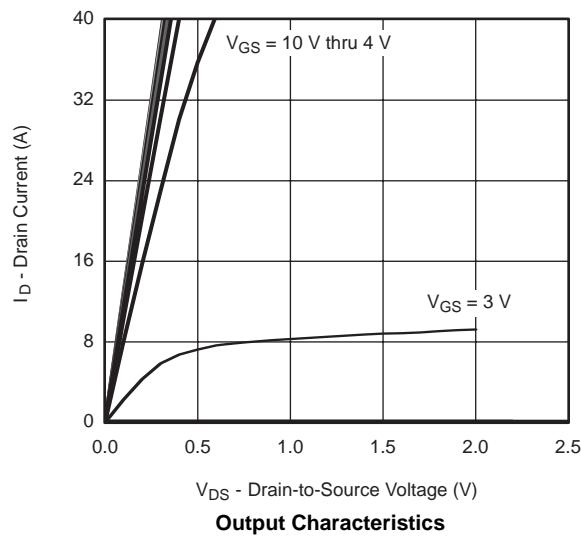
**SPECIFICATIONS**  $T_J = 25^\circ\text{C}$ , unless otherwise noted

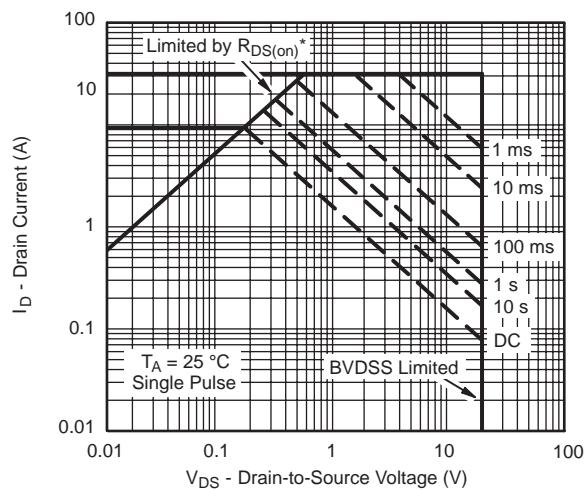
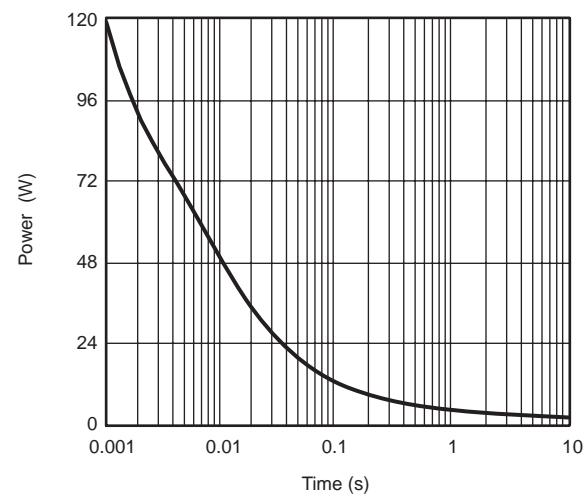
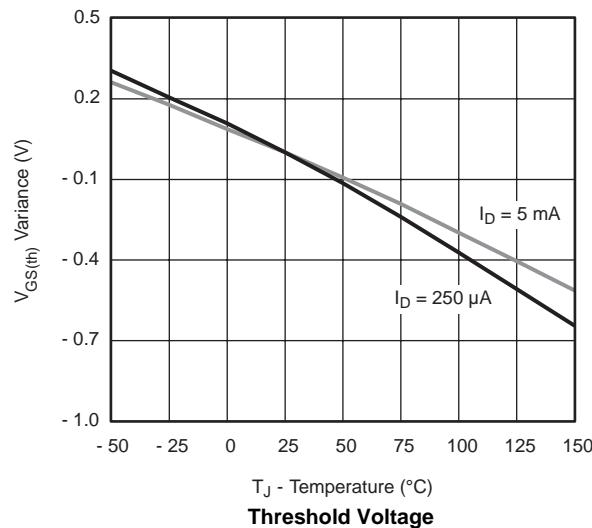
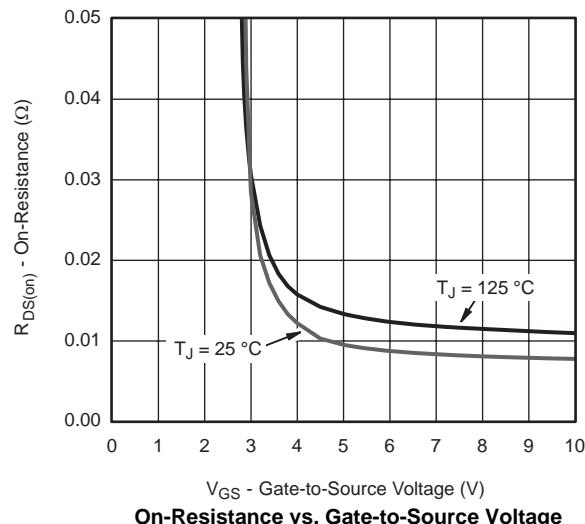
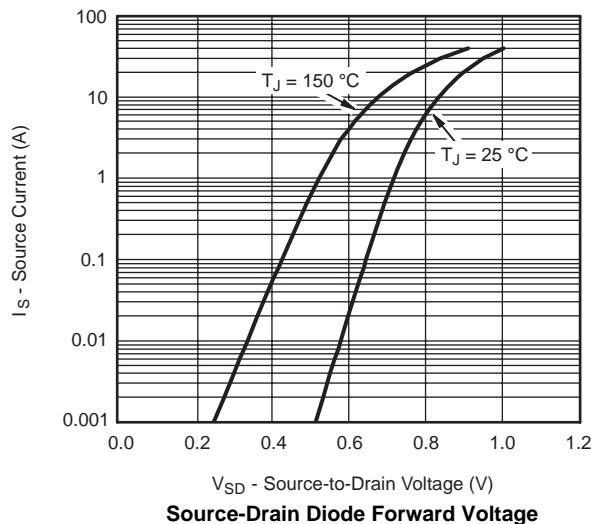
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
<b>Static</b>						
Drain-Source Breakdown Voltage	$V_{DS}$	$V_{GS} = 0 \text{ V}$ , $I_D = 250 \mu\text{A}$	20			V
$V_{DS}$ Temperature Coefficient	$\Delta V_{DS}/T_J$	$I_D = 250 \mu\text{A}$		22		$\text{mV/}^\circ\text{C}$
$V_{GS(\text{th})}$ Temperature Coefficient	$\Delta V_{GS(\text{th})}/T_J$			- 5.0		
Gate-Source Threshold Voltage	$V_{GS(\text{th})}$	$V_{DS} = V_{GS}$ , $I_D = 250 \mu\text{A}$	0.5		2.0	V
Gate-Source Leakage	$I_{GSS}$	$V_{DS} = 0 \text{ V}$ , $V_{GS} = \pm 20 \text{ V}$			$\pm 100$	nA
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = 20 \text{ V}$ , $V_{GS} = 0 \text{ V}$			1	$\mu\text{A}$
		$V_{DS} = 20 \text{ V}$ , $V_{GS} = 0 \text{ V}$ , $T_J = 55^\circ\text{C}$			5	
On-State Drain Current <sup>a</sup>	$I_{D(\text{on})}$	$V_{DS} \geq 5 \text{ V}$ , $V_{GS} = 10 \text{ V}$	12			A
Drain-Source On-State Resistance <sup>a</sup>	$R_{DS(\text{on})}$	$V_{GS} = 10 \text{ V}$ , $I_D = 10 \text{ A}$		0.011		$\Omega$
		$V_{GS} = 4.5 \text{ V}$ , $I_D = 7 \text{ A}$		0.012		
Forward Transconductance <sup>a</sup>	$g_{fs}$	$V_{DS} = 10 \text{ V}$ , $I_D = 10 \text{ A}$		26		S
<b>Dynamic<sup>b</sup></b>						
Input Capacitance	$C_{iss}$	$V_{DS} = 10 \text{ V}$ , $V_{GS} = 0 \text{ V}$ , $f = 1 \text{ MHz}$		850		$\text{pF}$
Output Capacitance	$C_{oss}$			305		
Reverse Transfer Capacitance	$C_{rss}$			120		
Total Gate Charge	$Q_g$	$V_{DS} = 10 \text{ V}$ , $V_{GS} = 10 \text{ V}$ , $I_D = 10 \text{ A}$		15	23	$\text{nC}$
				7.0	10	
Gate-Source Charge	$Q_{gs}$	$V_{DS} = 15 \text{ V}$ , $V_{GS} = 4.5 \text{ V}$ , $I_D = 10 \text{ A}$		2.2		
Gate-Drain Charge	$Q_{gd}$			2.1		
Gate Resistance	$R_g$	$f = 1 \text{ MHz}$	0.2	0.9	1.8	$\Omega$
Turn-On Delay Time	$t_{d(\text{on})}$	$V_{DD} = 10 \text{ V}$ , $R_L = 2 \Omega$ $I_D \geq 5 \text{ A}$ , $V_{GEN} = 4.5 \text{ V}$ , $R_g = 1 \Omega$		15	30	$\text{ns}$
Rise Time	$t_r$			11	22	
Turn-Off Delay Time	$t_{d(\text{off})}$			16	30	
Fall Time	$t_f$			8	16	
Turn-On Delay Time	$t_{d(\text{on})}$			10	20	
Rise Time	$t_r$			8	16	
Turn-Off Delay Time	$t_{d(\text{off})}$			16	30	
Fall Time	$t_f$			7	14	
<b>Drain-Source Body Diode Characteristics</b>						
Continuous Source-Drain Diode Current	$I_S$	$T_C = 25^\circ\text{C}$			12	$\text{A}$
Pulse Diode Forward Current	$I_{SM}$				36	
Body Diode Voltage	$V_{SD}$	$I_S = 3 \text{ A}$ , $V_{GS} = 0 \text{ V}$		0.77	1.2	V
Body Diode Reverse Recovery Time	$t_{rr}$	$I_F = 10 \text{ A}$ , $di/dt = 100 \text{ A}/\mu\text{s}$ , $T_J = 25^\circ\text{C}$		14	28	$\text{ns}$
Body Diode Reverse Recovery Charge	$Q_{rr}$			4.5	9	$\text{nC}$
Reverse Recovery Fall Time	$t_a$			5.5		$\text{ns}$
Reverse Recovery Rise Time	$t_b$			8.5		

Notes:

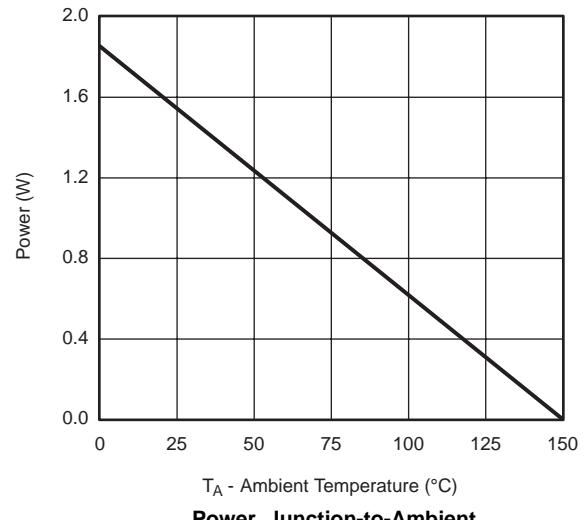
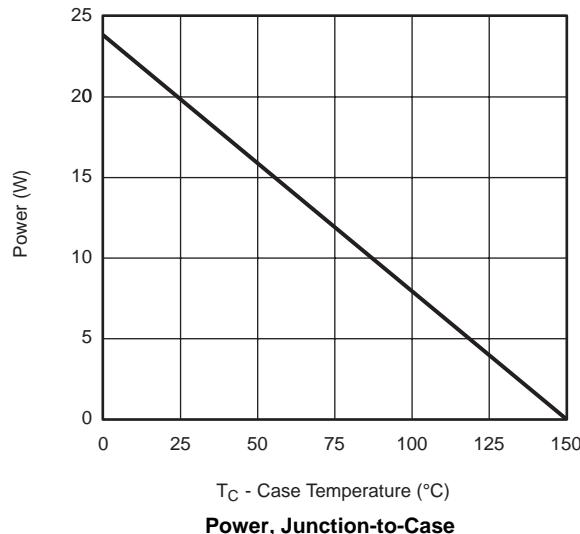
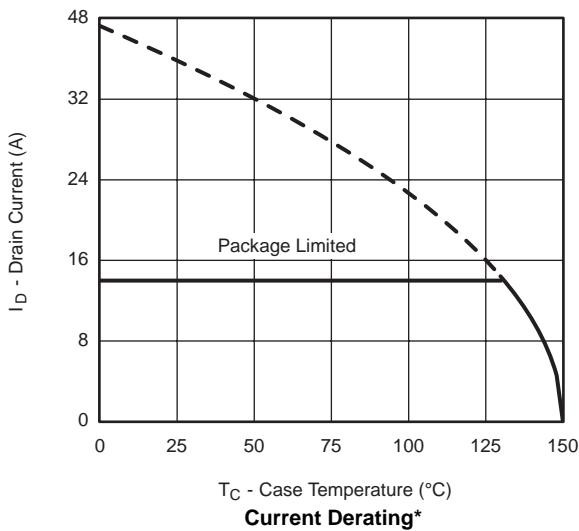
a. Pulse test; pulse width  $\leq 300 \mu\text{s}$ , duty cycle  $\leq 2 \%$ .  
 b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

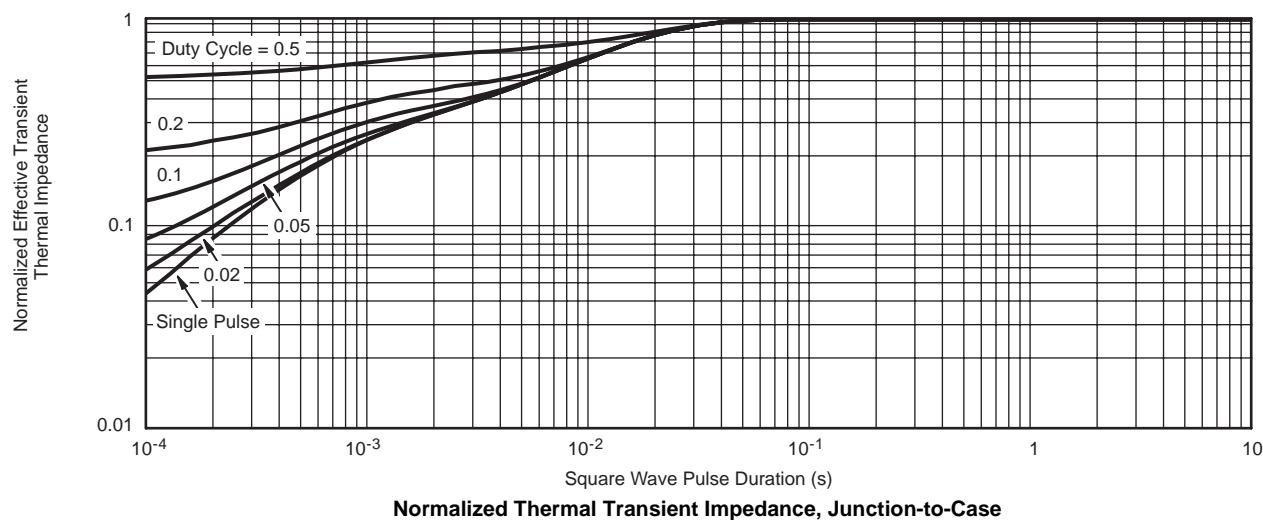
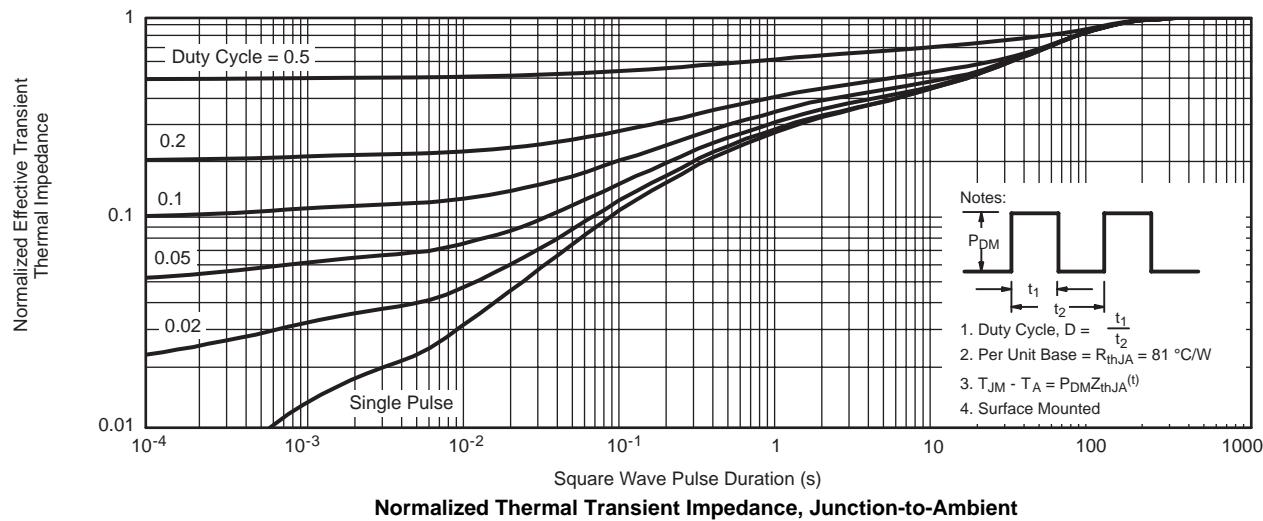
**TYPICAL CHARACTERISTICS** 25 °C, unless otherwise noted


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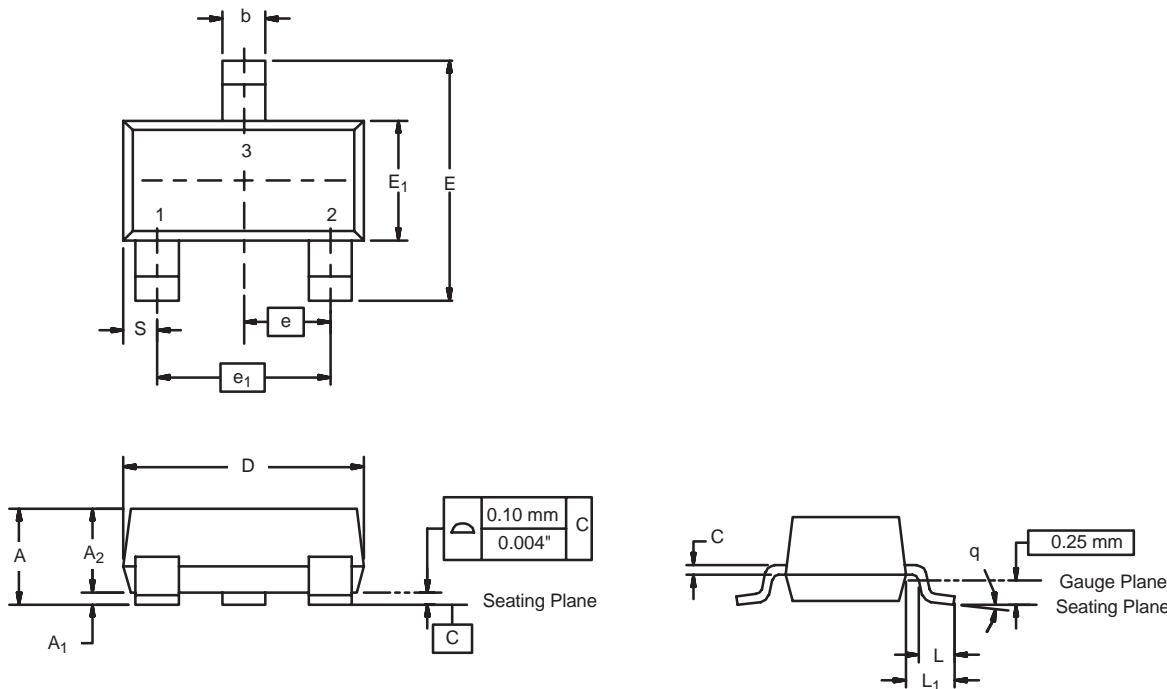
\*  $V_{GS} >$  minimum  $V_{GS}$  at which  $R_{DS(on)}$  is specified

**TYPICAL CHARACTERISTICS** 25 °C, unless otherwise noted


\* The power dissipation  $P_D$  is based on  $T_{J(\max)} = 150$  °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

**TYPICAL CHARACTERISTICS** 25 °C, unless otherwise noted


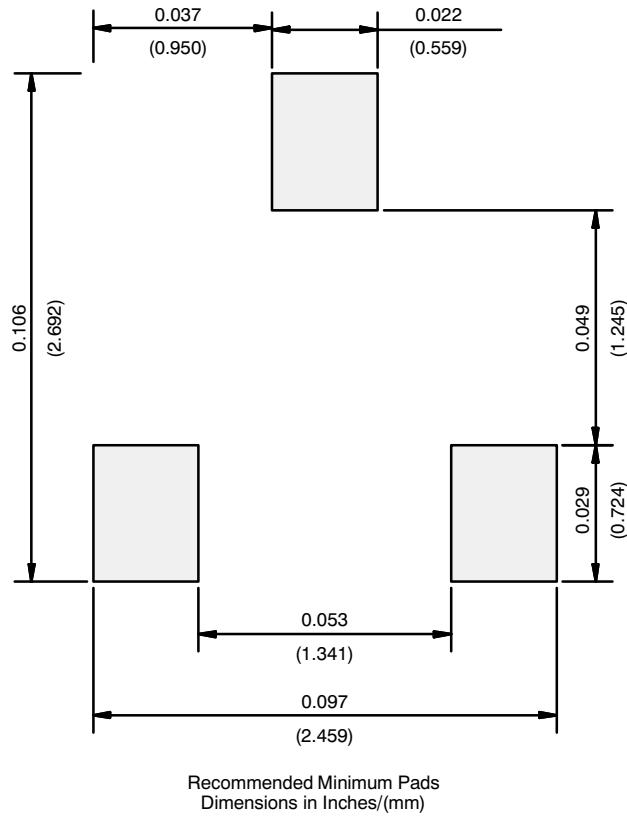
## SOT-23 : 3-LEAD



Dim	MILLIMETERS		INCHES	
	Min	Max	Min	Max
A	0.89	1.12	0.035	0.044
A <sub>1</sub>	0.01	0.10	0.0004	0.004
A <sub>2</sub>	0.88	1.02	0.0346	0.040
b	0.35	0.50	0.014	0.020
c	0.085	0.18	0.003	0.007
D	2.80	3.04	0.110	0.120
E	2.10	2.64	0.083	0.104
E <sub>1</sub>	1.20	1.40	0.047	0.055
e	0.95 BSC		0.0374 Ref	
e <sub>1</sub>	1.90 BSC		0.0748 Ref	
L	0.40	0.60	0.016	0.024
L <sub>1</sub>	0.64 Ref		0.025 Ref	
S	0.50 Ref		0.020 Ref	
q	3°	8°	3°	8°

ECN: S-03946-Rev. K, 09-Jul-01  
 DWG: 5479

## RECOMMENDED MINIMUM PADS FOR SOT-23



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